

Wrocław University of Science and Technology

Advanced Optoelectronic

project





Wrocław University of Science and Technology

HR EXCELLENCE IN RESEARCI

p-contact

Advanced Optoelectronic project

Introduction part II



Output aperture

AR coating

Oxide-confined layer

.Passivation laye

n-DBR

tive QWS

GaAs substrate

n-contact

Simulation software by: Crosslight Software Inc.

http://crosslight.com/

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Introduction

LED structure

✤.sol file

MSM structure

.layer and .sol files



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LED structure

Defining the device structure – cross section

1
$$\mu$$
m - Al_{0.5}Ga_{0.5}As - p=1.0×10²⁴ m⁻³

0.2 μm - GaAs - undoped; active region

1 μm - Al_{0.5}Ga_{0.5}As - n=1.0×10²⁴ m⁻³





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.sol file

Defining the device structure – test1.sol file

Şfile:test1.sol
begin
load_mesh mesh_inf=test1.msh
include file=test1.mater
include file=test1.doping
output sol_outf=test1.out
newton_par damping_step=5. max_iter=100 print_flag=3
use_sor max_iter=3000 print_sor=noprint
init_wave &&
length= 0.2000E+03 backg_loss=500. &&
boundary_type=[2 2 1 1] init_wavel= 0.8300E+00 mirror_ref=0.32 &&
wavel_range=[0.8100E+00 0.8500E+00]
equilibrium
newton_par damping_step=1. print_flag=3
<pre>scan var=voltage_1 value_to= -0.1345E+01 print_step= 0.1345E+01 &&</pre>
init_step= 0.2689E+00 min_step=1.e-5 max_step=0.5
<pre>scan var=current_1 value_to= 0.2500E+03 print_step= 0.2500E+03 &&</pre>
init_step= 0.2500E+01 min_step=1.e-5 max_step= 0.2500E+02
end



.sol file

\$file:test1.sol

load_mesh_nesh_inf=test1.msh

include file=test1.mater

include file=test1.doping

output sol outf=test1 out

begin



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The **.msh** file will be loaded into simulation data.

The different files with material information will

be merged with input data.

Definition of base name for output data files.

Defining the device structure – test1.sol file





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Define a basic 1D mode solver.

newton_par damping_step=5. max_iter=100 print_flag=3

use_sor nax_iter=3000 print_sor=noprint

init_wave &&

.sol file

length= 0.2000E+03 backg_loss=500. &&

boundary_type=[2211] init_wavel= 0.8300E+00 mirror_ref=0.32 &&

Defining the device structure – test1.sol file

wavel_range=[0.8100E+00 0.8500E+00]

Defines the boundary conditions for the waveguide as well as other critical parameters for the device (length, mirror reflectivity, background losses, etc...)





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It calls the Newton solver to get the initial solution of the device under thermal equilibrium conditions: this means only the Poisson equation is solved and the net current is zero for both electrons and holes. This is a required first step before bias can be applied.

It calls the Newton solver and find the state of the device under bias.

equilibrium

.sol file

newton_par_damping_step=1. print_flag=3

scan vir=voltage_1 value_to= -0.1345E+01 print_step= 0.1345E+01 &&

Defining the device structure – test1.sol file

init_step= 0.2689E+00 min_step=1.e-5 max_step=0.5

scan var=current_1 value_to= 0.2500E+03 print_step= 0.2500E+03 &&

_init_step= 0.2500E+01 min_step=1.e-5 max_step= 0.2500E+02

The variable controls which electrode is biased as well as the type of bias which is applied

end



MSM structure



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MSM .layer file

Defining the device structure – msm.layer file

begin layer \$ column column num=1 w=0.5 mesh num=4 r=0.8 && column column num=2 w=1.5 mesh num=19 r=-1.3 && xpoint left=yes xpoint right=yes column column num=3 w=0.5 mesh num=4 r=1.2 && xpoint left=yes Ś \$ The lower current blocking layer. Ś layer mater macro name=algaas var1=0.3 column num=1 layer mater macro name=algaas var1=0.3 column num=2 layer mater macro name=algaas var1=0.3 column num=3 laver d=0.15 n=4 r=1. && n doping1=1.e21 n doping2=1.e21 n doping3=1.e21 && xp2=1 \$ \$ The main part of the GaAs MSM. layer mater macro name=gaas column num=1 layer mater macro name=gaas column num=2 layer mater macro name=gaas column num=3 layer d=0.5 n=8 r=0.8 && n doping1=1.e21 n doping2=1.e21 n doping3=1.e21 && xp1=1 xp2=1 \$ These are the two electrodes. top contact column num=1 from=0 to=0.5 contact num=1 top contact column num=3 from=0 to=0.5 contact num=2

Define three columns so that extra mesh lines can be allocated near the electrodes. For AaPSYS simulation Schottky contacts require extra mesh lines so that the barrier height can be accurtely defined.

end layer





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MSM .sol file – part I

Defining the device structure – msm.sol file

```
$file:msm.sol
$*******
begin
load mesh mesh inf=msm.msh
$
$ Equilibrium solution.
$
newton par damping step=5. var tol=1.e-9 res tol=1.e-9 &&
equilibrium
$
$ Ramp up the DC bias to 5 volts.
Ś
newton par damping step=1. var tol=1.e-4 res tol=1.e-4 &&
max iter=30 opt iter=15 stop iter=15 print flag=3
scan var=voltage 1 value to=-5. print step=5. &&
init step=0.2 min step=1.e-5 max step=1.0
$ Turn on the Gaussian optical pulse with
$ pulse width of 4 ps.
Ś
scan var num=2 2 variables=(time light) &&
value to=50.D-12 print step=50.D-12 &&
init step=1.D-14 min step=1.d-18 max step=1.D-12 &&
relation=gaussian gsn dt=4.e-12
Ś
$ We wait some more time until the MSM settles down.
$
scan var=time value to=300.D-12 print step=300.D-12 &&
init step=1.D-12 min step=1.d-15 max step=10.D-12
```





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```
MSM .sol file – part II
Ŝ
$ Define the incident light here. The profile is used
$ to block out the light for the area under the metal electrodes.
light power incident power=3.29e7 wavelength=0.82 &&
profile=(0.5, 2.0, 0.01, 0.01)
$
$ Put optical coatings on top of device, if you wish.
$ It may be used to optimize the optical interference inside
$ the MSM.
Ś
Soptic coating thickness=0.147 real index=2.05 imag index=0.
$
back reflection real refl=0. imag refl=0.
output sol outf=msm.out
$ ****************************
$ Define the barrier potential for the Schottky contacts.
Ś
contact type=schottky barrier=-0.83 num=1
contact type=schottky barrier=-0.83 num=2
Ś
$ Include the doping and material description generated
$ by msm.layer.
$
include file=msm.doping
include file=msm.mater
$
$ Be sure to define the absorption for the GaAs layer. Otherwise
$ there will be no response from the detector
absorption value=1.1e6 mater=2
$
```

end



End of Introduction part II